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BUK9E6R1-100E

N-channel TrenchMOS logic level FET

11 September 2012

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{gst(th)} rating of greater than 0.5V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

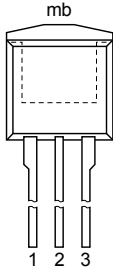
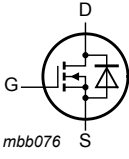
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; Fig. 1	[1]	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2	-	-	349	W
Static characteristics						
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	4.85	6.1	mΩ
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 80 V; Fig. 13 ; Fig. 14	-	51	-	nC

[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>I2PAK (SOT226)</p>	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK9E6R1-100E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK9E6R1-100E	BUK9E6R1-100E

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	100	V	
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V	
V_{GS}	gate-source voltage	$T_j \leq 175\text{ °C}$; Pulsed	[1][2]	-15	15	V
		$T_j \leq 175\text{ °C}$; DC		-10	10	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 5\text{ V}$; Fig. 1	[3]	-	120	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 5\text{ V}$; Fig. 1		-	103	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4	-	576	A	
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2	-	349	W	

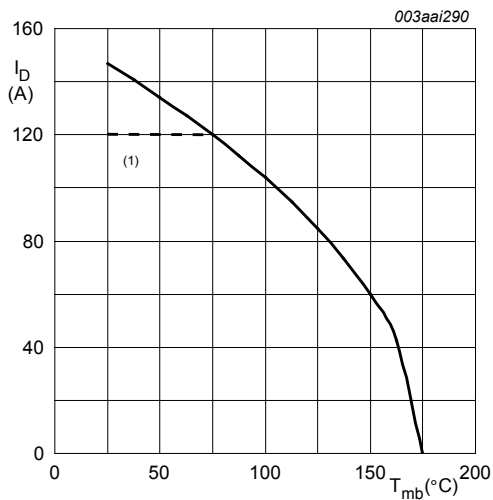
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[3]	-	120	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	576	A
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 120 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 3	[4][5]	-	387	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_j and or V_{GS}
- [3] Continuous current is limited by package.
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [5] Refer to application note AN10273 for further information.



(1) Capped at 120A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 5V$$

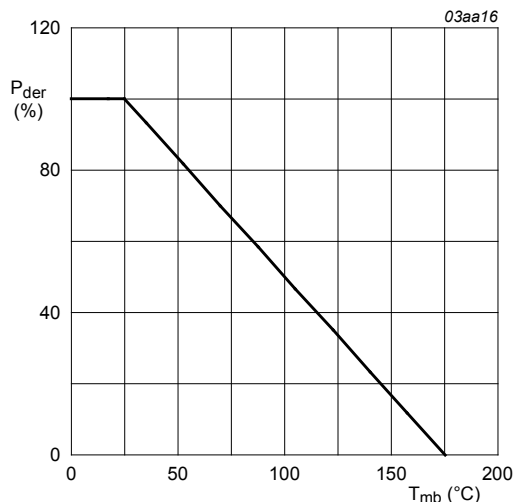


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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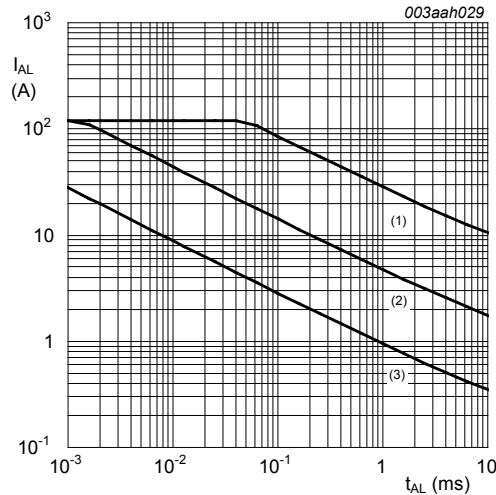


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 150^{\circ}C$; (3) Repetitive Avalanche

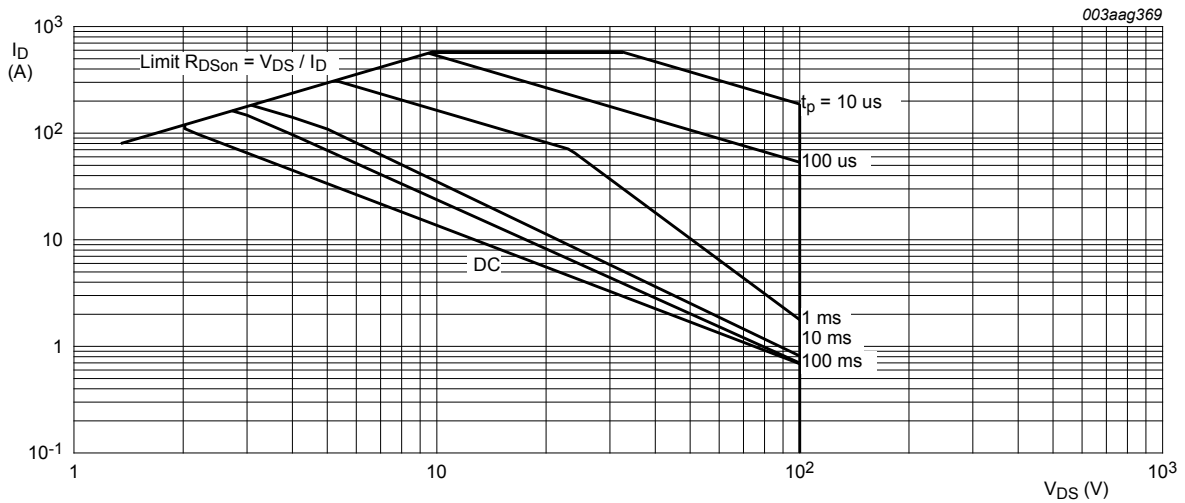


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	65	-	K/W

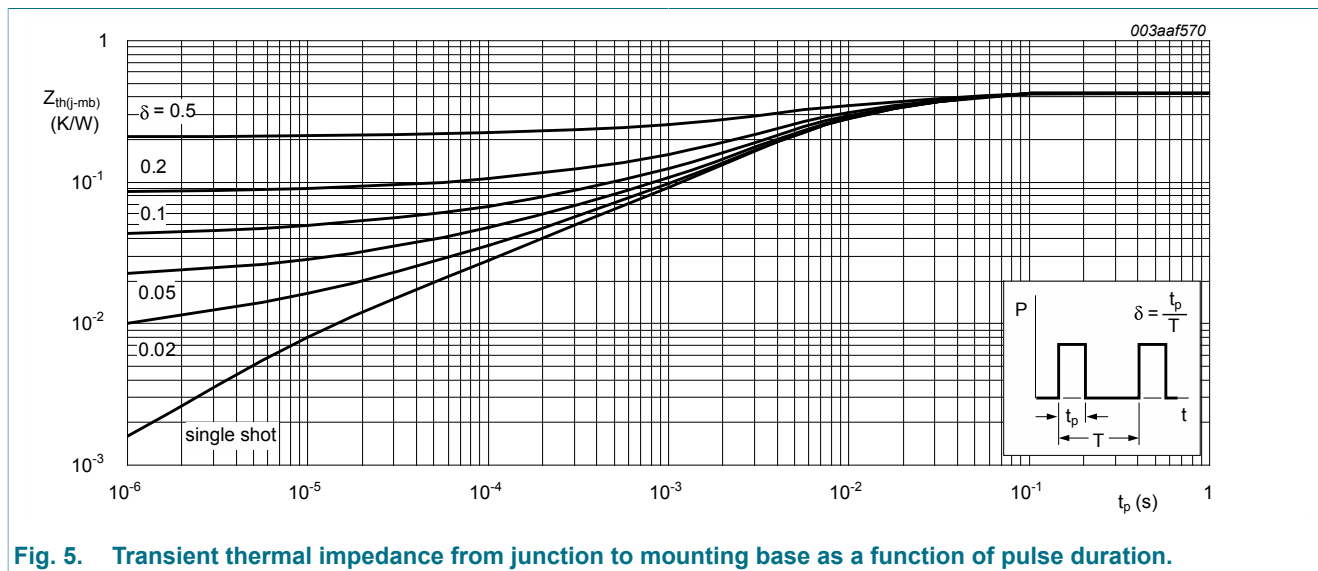


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

7. Characteristics

Table 7. Characteristics

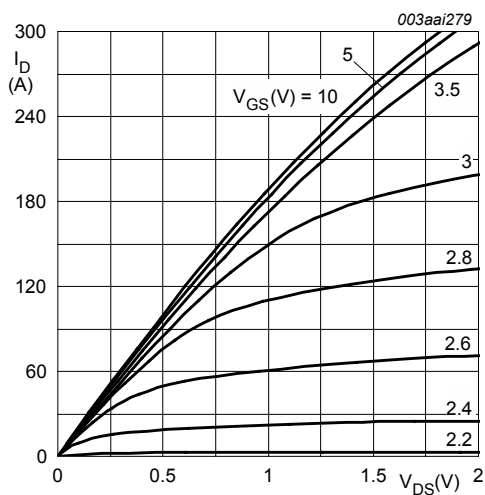
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$ Fig. 9	0.5	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.05	1	μA
		$V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 25 A; T_j = 25 \text{ }^\circ C;$ Fig. 11	-	4.85	6.1	m Ω
		$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C;$ Fig. 11	-	4.7	5.9	m Ω
		$V_{GS} = 5 V; I_D = 25 A; T_j = 175 \text{ }^\circ C;$ Fig. 12; Fig. 11	-	-	16.8	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 80 V; V_{GS} = 5 V;$ Fig. 13; Fig. 14	-	133	-	nC
Q_{GS}	gate-source charge		-	23	-	nC

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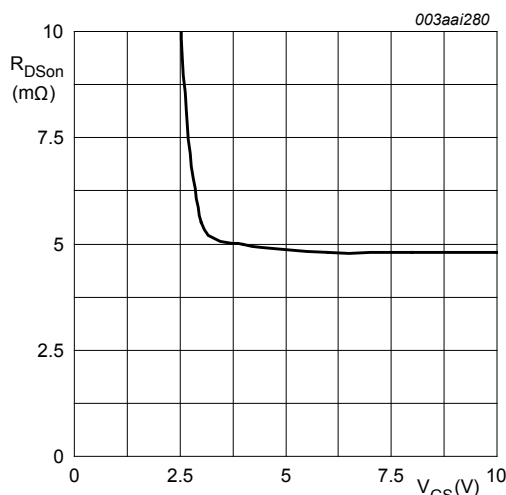
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{GD}	gate-drain charge		-	51	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C};$ Fig. 15	-	13100	17460	pF
C_{oss}	output capacitance		-	725	870	pF
C_{rss}	reverse transfer capacitance		-	450	620	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 80\text{ V}; R_L = 3.2\text{ }\Omega; V_{GS} = 5\text{ V}; R_{G(ext)} = 5\text{ }\Omega$	-	81	-	ns
t_r	rise time		-	168	-	ns
$t_{d(off)}$	turn-off delay time		-	237	-	ns
t_f	fall time		-	148	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to centre of die	-	2.5	-	nH
		from drain lead 6mm from package to centre of die	-	4.5	-	nH
L_S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 16	-	0.77	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; dI_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}$	-	70	-	ns
Q_r	recovered charge		-	202	-	nC



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



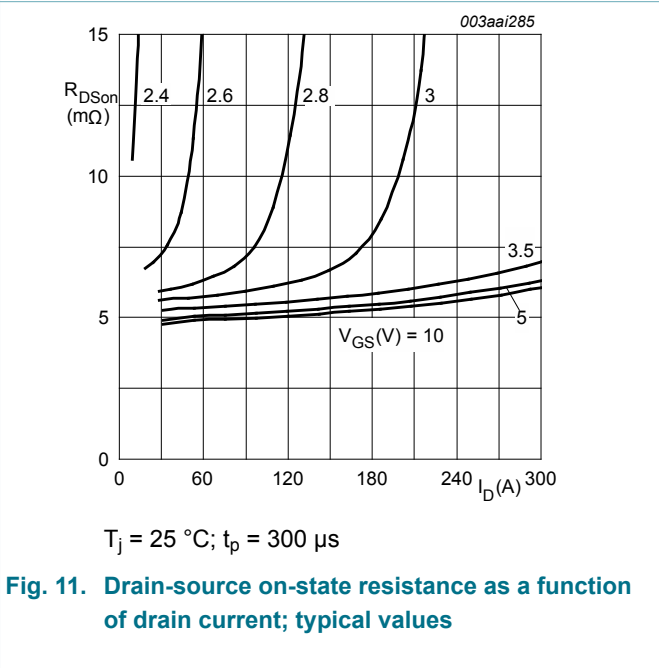
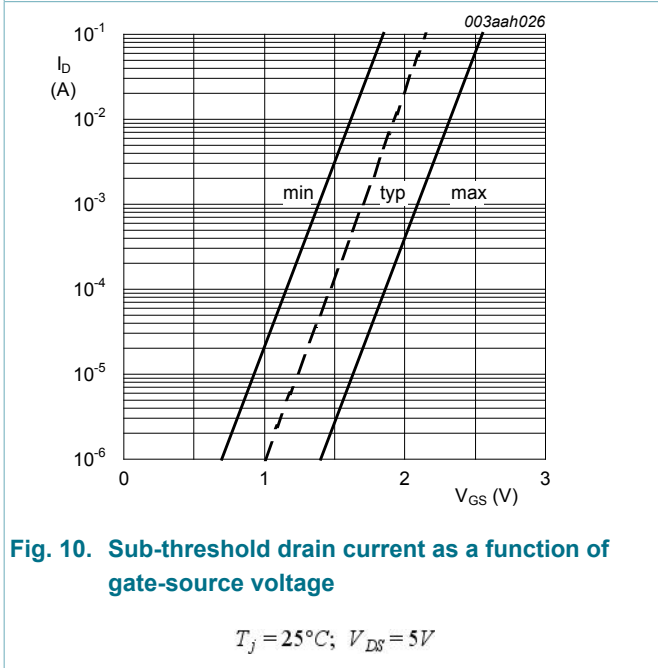
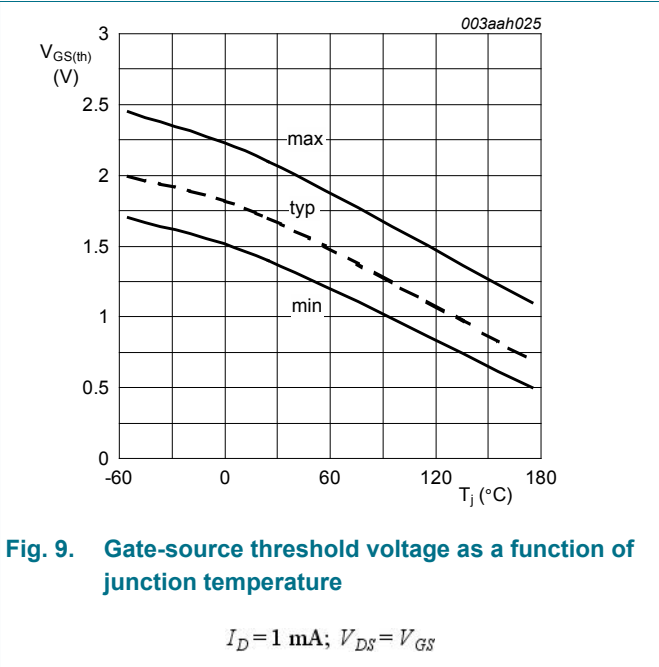
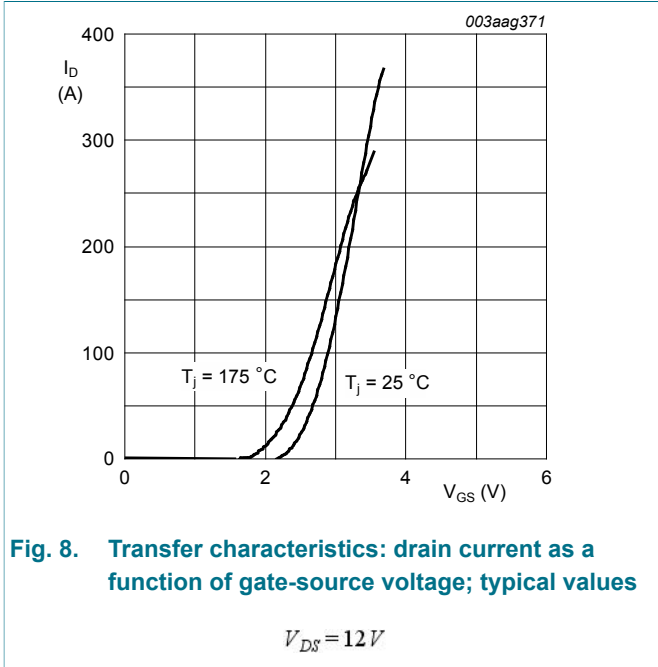
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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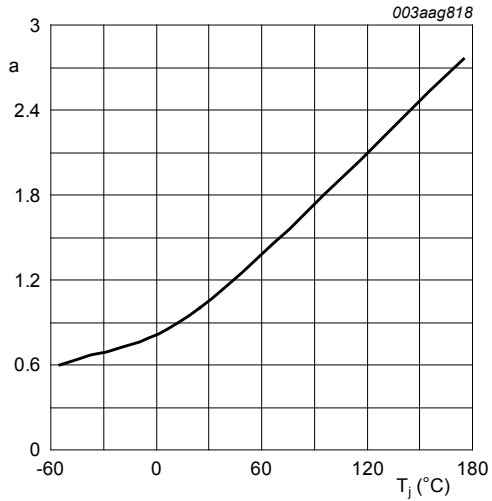
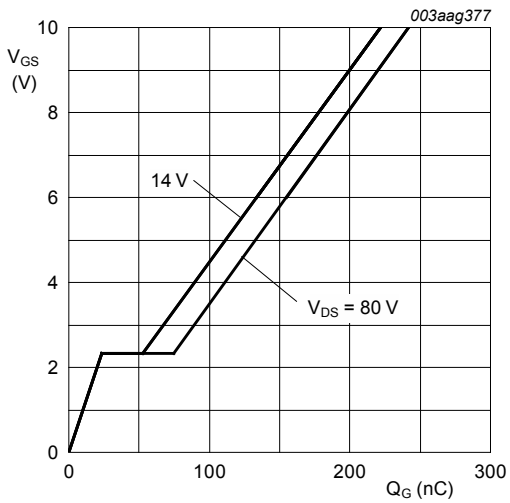


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25\text{ }^\circ\text{C})}}$$



$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

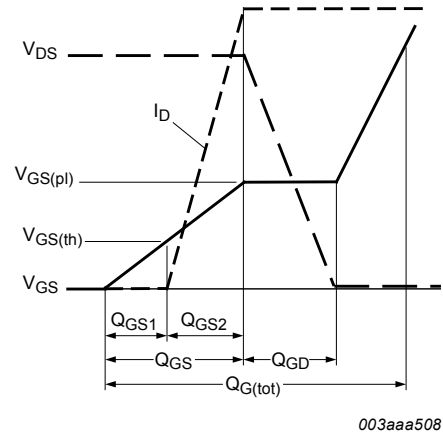
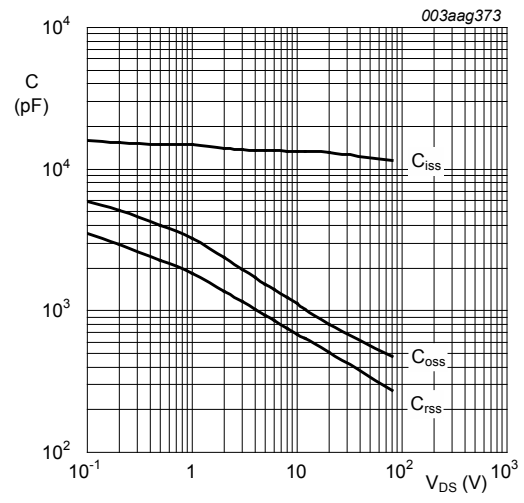
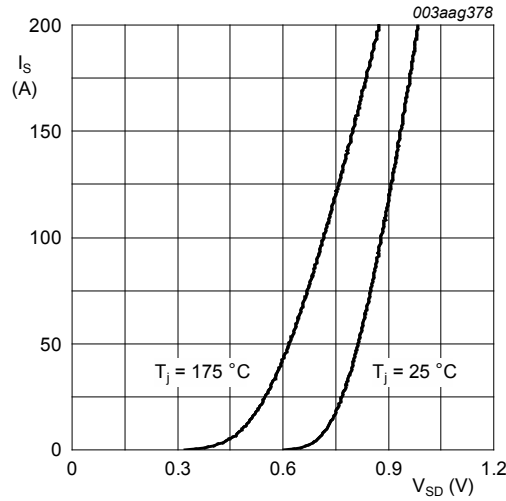


Fig. 13. Gate charge waveform definitions



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

8. Package outline

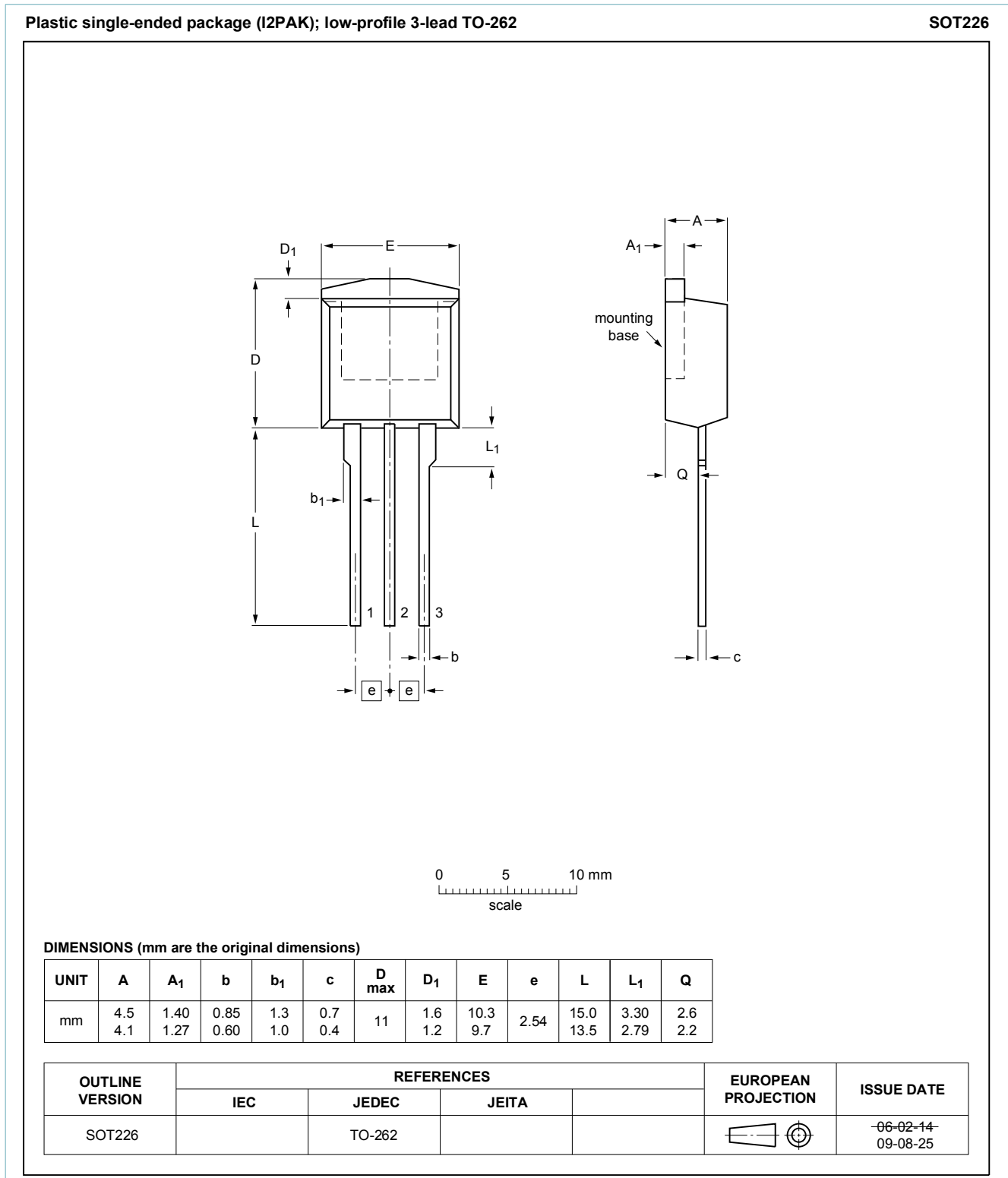


Fig. 17. Package outline I2PAK (SOT226)

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9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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